

	Title	Authors	Year	Source title	Vol	Art. No.	Pg start	Pg end
203	SYNAPSE: An international roadmap to large brain imaging	Stampfl A.P.J., Liu Z., Hu J., Sawada K., Takano H., Kohmura Y., Ishikawa T., Lim J.-H., Je J.-H., Low C.-M., Teo A., Tok E.S., Tan T.W., Ban K., Libedinsky C., Tan F.C.K., Chen K.-P., Yang A.-C., Chuang C.-C., Chen N.-Y., Shih C.-T., Lee T.-K., Yang D.-N., Lai H.-C., Shuai H.-H., Cheng C.-C., Ching Y.-T., Li C.-W., Chang C.-C., Lo C.-C., Chiang A.-S., Recur B., Petibois C., Cheng C.-L., Chen H.-H., Yang S.-M., Hwu Y., Rojviriyi C., Rugmai S., Rujirawat S., Margaritondo G.	2023	Physics Reports	999		1	60
202	Anomalous Ferromagnetism of quasiparticle doped holes in cuprate heterostructures revealed using resonant soft X-ray magnetic scattering	Ong B.L., Jayaraman K., Diao C., Whitcher T.J., Jain A., Hung H., Breese M.B.H., Tok E.S., Rusydi A.	2022	Nature Communications	13	4639		
201	The new X-ray/visible microscopy MAXWELL technique for fast three-dimensional nanoimaging with isotropic resolution	Kohmura Y., Yang S.-M., Chen H.-H., Takano H., Chang C.-J., Wang Y.-S., Lee T.-T., Chiu C.-Y., Yang K.-E., Chien Y.-T., Hu H.-M., Su T.-L., Petibois C., Chen Y.-Y., Hsu C.-H., Chen P., Hueng D.-Y., Chen S.-J., Yang C.L., Chin A.-L., Low C.-M., Tan F.C.K., Teo A., Tok E.S., Cai X.X., Lin H.-M., Boeckl J., Stampfl A.P., Yamada J., Matsuyama S., Ishikawa T., Margaritondo G., Chiang A.-S., Hwu Y.	2022	Scientific Reports	12	9668		
200	Erratum: A new spin-correlated plasmon in novel highly oriented single-crystalline gold quantum dots (Nano Letters (2021) 21:18 (7448-7456))	Ong B.L., Naradipa M.A., Fauzi A.D., Majidi M.A., Diao C., Kurumi S., Das P.K., Xiao C., Yang P., Breese M.B.H., Ong S.W., Tan K.M., Tok E.S., Rusydi A.	2021	Nano Letters	21		9364	
199	A New Spin-Correlated Plasmon in Novel Highly Oriented Single-Crystalline Gold Quantum Dots	Ong B.L., Naradipa M.A., Fauzi A.D., Majidi M.A., Diao C., Kurumi S., Das P.K., Xiao C., Yang P., Breese M.B.H., Ong S.W., Tan K.M., Tok E.S., Rusydi A.	2021	Nano Letters	21		7448	7456
198	High-resolution fast-tomography brain-imaging beamline at the Taiwan Photon Source	Chen H.H., Yang S.-M., Yang K.-E., Chiu C.-Y., Chang C.-J., Wang Y.-S., Lee T.-T., Huang Y.-F., Chen Y.-Y., Petibois C., Chang S.-H., Cai X., Low C.-M., Tan F.C.K., Teo A., Tok E.S., Lim J.-H., Je J.-H., Kohmura Y., Ishikawa T., Margaritondo G., Hwu Y.	2021	Journal of Synchrotron Radiation	28		1662	1668
197	Important roles of native-oxides on the electronic band offsets at Ge-oxide/Ge(0 0 1) heterojunction in ambient environment	Ong B.L., Ong S.W., Rusydi A., Tok E.S.	2020	Applied Surface Science	530	147256		
196	A synchrotron X-ray imaging strategy to map large animal brains	Chin A.-L., Yang S.-M., Chen H.-H., Li M.-T., Lee T.-T., Chen Y. J., Lee T.-K., Petibois C., Cai X., Low C.-M., Tan F.C.K., Teo A., Tok E.S., Ong E.B.L., Lin Y.-Y., Lin I.-J., Tseng Y.-C., Chen N.-Y., Shih C.-T., Lim J.-H., Lim J., Je J.-H., Kohmura Y., Ishikawa T., Margaritondo G., Chiang A.-S., Hwu Y.	2020	Chinese Journal of Physics	65		24	32
195	Gold nano-mesh synthesis by continuous-flow X-ray irradiation	Li M.-T., Lai S.-F., Yang S.-M., Chen Y.-S., Chen Y.-J., Tok E.S., Margaritondo G., Hwu Y.	2019	Journal of Synchrotron Radiation	26		1929	1935
194	A Fluorographene-Based Synaptic Transistor	Liu B., Hong M.-C., Sahoo M., Ong B.L., Tok E.S., Di M., Ho Y. P., Liang H., Bow J.-S., Liu Z., Wang J.-C., Hou T.-H., Lai C.-S.	2019	Advanced Materials Technologies	4	1900422		
193	Optical and chemical stability of sputtered-Au nanoparticles and film in ambient environment	Ong S.W., Ong B.L., Tok E.S.	2019	Applied Surface Science	488		753	762
192	Spatially mapping work function changes and defect evolution in the fluorination of graphene	Ong B.L., Ong S.W., Liu B., Lai C.S., Johll H., Kang H.C., Tok E.S.	2019	2019 IEEE 9th International Nanoelectronics Conferences, INEC 2019		8853850		
191	In-situ real-time observation of sn-rich dots and wires during annealing of GeSn epitaxial films	Ong S.W., Ong B.L., Kang H.C., Tok E.S.	2019	2019 IEEE 9th International Nanoelectronics Conferences, INEC 2019		8853861		
190	Kinetics during endotaxial growth of CoSi 2 nanowires and islands on Si(0 0 1)	Ong B.L., Tok E.S.	2019	Applied Surface Science	466		583	591
189	Graphene as a reducing agent for electroless plating of metal	Narula U., Tan C.M., Tok E.S.	2019	2018 IEEE 15th Nanotechnology Materials and Devices Conference, NMDC 2018		8605846		

188	Blue micro-highlighting in alumina-GO hybrid empowered by focused laser beam	Seah M.H.R., Lim S.X., Tok E.S., Sow C.-H.	2019	Journal of Luminescence	205		357	366
187	Laser assisted blending of Ag nanoparticles in an alumina veil: a highly fluorescent hybrid	Lim S.X., Koon G.K.W., Zhang Z., Castro Neto A.H., Tok E.S., Sow C.-H.	2018	Nanoscale	10		18145	18152
186	Distribution of Sn in Strained Ge <sub>1-x</sub> Sn <sub>x</sub> (001): The Effect of Surface Passivation	Ong S.W., Tok E.S.	2018	2018 IEEE 8th International Nanoelectronics Conferences, INEC 2018		8441914	31	32
185	Tuning endotaxial growth of CoSi <sub>2</sub> nanowires and nanodots	Ong B.L., Tok E.S.	2018	2018 IEEE 8th International Nanoelectronics Conferences, INEC 2018		8441929	35	36
184	Metal on Graphenated Metal for VLSI Interconnects	Narula U., Tan C.M., Tok E.S.	2018	Advanced Materials Interfaces	5	1800270		
183	Impact of Electrical Conductivity on the Electrochemical Performances of Layered Structure Lithium Trivanadate (LiV <sub>3</sub> -xM <sub>x</sub> O <sub>8</sub> , M= Zn/Co/Fe/Sn/Ti/Zr/Nb/Mo, x = 0.01-0.1) as Cathode Materials for Energy Storage	Kumar P.S., Ayyasamy S., Tok E.S., Adams S., Reddy M.V.	2018	ACS Omega	3		3036	3044
182	Ru/ZrO <sub>2</sub> Catalysts for Transfer Hydrogenation of Levulinic Acid with Formic Acid/Formate Mixtures: Importance of Support Stability	Gao Y., Zhang H., Han A., Wang J., Tan H.-R., Tok E.-S., Jaenicke S., Chuah G.-K.	2018	ChemistrySelect	3		1343	1351
181	Templating nanotraffic light-dynamic tricoloured blinking silver nanoclusters on a graphene oxide film	Lim S.X., Lee Y.Z., Gao N., Lu J., Xu Q., Tok E.S., Sow C.H.	2018	Journal of Materials Chemistry C	6		4641	4648
180	Thermal stability of germanium-tin (GeSn) fins	Lei D., Lee K.H., Bao S., Wang W., Masudy-Panah S., Tan C.S., Tok E.S., Gong X., Yeo Y.-C.	2017	Applied Physics Letters	111	252103		
179	Kinetics of plasma oxidation of germanium-tin (GeSn)	Wang W., Lei D., Dong Y., Zhang Z., Pan J., Gong X., Tok E.-S., Yeo Y.-C.	2017	Applied Surface Science	425		95	99
178	Digital etch technique for forming ultra-scaled germanium-tin (Ge <sub>1-x</sub> Sn <sub>x</sub> ) fin structure	Wang W., Lei D., Dong Y., Gong X., Tok E.S., Yeo Y.-C.	2017	Scientific Reports	7	1835		
177	Tunable Fluorescence Properties Due to Carbon Incorporation in Zinc Oxide Nanowires	Lim K.Y., Linghu J., Chi X., Yuan K., Hew K.M., Zheng M., Yang M., Tok E.S., Rusydi A., Yu X., Chen W., Feng Y.P., Sow C.H.	2017	Advanced Optical Materials	5	1700381		
176	In-situ growth of HfO <sub>2</sub> on clean 2H-MoS <sub>2</sub> surface: Growth mode, interface reactions and energy band alignment	Chen C.P., Ong B.L., Ong S.W., Ong W., Tan H.R., Chai J.W., Zhang Z., Wang S.J., Pan J.S., Harrison L.J., Kang H.C., Tok E.S.	2017	Applied Surface Science	420		523	534
175	Characterization of the electronic structure and thermal stability of HfO <sub>2</sub> /SiO <sub>2</sub> /Si gate dielectric stack	Duan T.L., Pan L., Zhang Z., Tok E.S., Pan J.S.	2017	Surface and Interface Analysis	49		776	780
174	Molecular nanocorrals on Si(111)-(7×7): Temperature-dependent site selectivity	Mao W., He J.H., Xi Y.J., Chen W., Wu K., Zhang C., Tok E.S., Xu G.Q.	2016	Journal of Physical Chemistry C	120		24780	24788
173	Photoconductivity of interconnected nanowires and their electromagnetic-circuit co-simulation	Mukherjee B., Simsek E., Varghese B., Zheng M., Tok E.S., Sow C.H.	2016	2016 USNC-URSI Radio Science Meeting (AP-S Symposium), Proceedings		7588513	63	64

172	Fluorescence Concentric Triangles: A Case of Chemical Heterogeneity in WS <sub>2</sub> Atomic Monolayer	Liu H., Lu J., Ho K., Hu Z., Dang Z., Carvalho A., Tan H.R., Tok E.S., Sow C.H.	2016	Nano Letters	16		5559	5567
171	Investigation of Ni Magnetic Micro-Seed in SAC 305 Solder for Inductive Heating Applicability	Krishnan R.G., Ke X., Kumar S.A., Tok E.S., Raaj G.Y., Srayes G., Pecht M.	2016	Proceedings - Electronic Components and Technology Conference	16-Aug	7545728	2196	2202
170	Photoconductivity in VO <sub>2</sub> -ZnO inter-nanowire junction and nanonetwork device	Mukherjee B., Varghese B., Zheng M., Tok E.S., Simsek E., Sow C.H.	2016	Nanoscience and Nanotechnology Letters	8		492	497
169	Enhanced Photoresponse from Phosphorene-Phosphorene-Suboxide Junction Fashioned by Focused Laser Micromachining	Lu J., Carvalho A., Wu J., Liu H., Tok E.S., Neto A.H.C., Özyilmaz B., Sow C.H.	2016	Advanced Materials	28		4090	4096
168	Interactions between lasers and two-dimensional transition metal dichalcogenides	Lu J., Liu H., Tok E.S., Sow C.-H.	2016	Chemical Society Reviews	45		2494	2515
167	Germanium-tin interdiffusion in strained Ge/GeSn multiple-quantum-well structure	Wang W., Dong Y., Zhou Q., Tok E.S., Yeo Y.-C.	2016	Journal of Physics D: Applied Physics	49	225102		
166	Endotaxial growth of CoSi <sub>2</sub> nanowires on Si(001) surface: The influence of surface reconstruction	Ong B.L., Ong S.W., Tok E.S.	2016	Surface Science	647		84	89
165	In-situ gallium-doping for forming p+ germanium-tin and application in germanium-tin p-i-n photodetector	Wang W., Vajandar S., Lim S.L., Dong Y., D'Costa V.R., Osipowicz T., Tok E.S., Yeo Y.-C.	2016	Journal of Applied Physics	119	155704		
164	Growth and characterization of highly tensile strained Ge <sub>1-x</sub> Sn <sub>x</sub> formed on relaxed In <sub>y</sub> Ga <sub>1-y</sub> P buffer layers	Wang W., Loke W.K., Yin T., Zhang Z., D'Costa V.R., Dong Y., Liang G., Pan J., Shen Z., Yoon S.F., Tok E.S., Yeo Y.-C.	2016	Journal of Applied Physics	119	125303		
163	Dehydrogenation of Alcohols over Alumina-Supported Silver Catalysts: The Role of Oxygen in Hydrogen Formation	Liu H., Tan H.-R., Tok E.S., Jaenicke S., Chuah G.-K.	2016	ChemCatChem	8		968	975
162	Ge <sub>0.83</sub> Sn <sub>0.17</sub> p-channel metal-oxide-semiconductor field-effect transistors: Impact of sulfur passivation on gate stack quality	Lei D., Wang W., Zhang Z., Pan J., Gong X., Liang G., Tok E.-S., Yeo Y.-C.	2016	Journal of Applied Physics	119	24502		
161	Enhanced activity of H <sub>2</sub> O <sub>2</sub> -treated copper(ii) oxide nanostructures for the electrochemical evolution of oxygen	Handoko A.D., Deng S., Deng Y., Fai Cheng A.W., Chan K.W., Tan H.R., Pan Y., Tok E.S., Sow C.H., Yeo B.S.	2016	Catalysis Science and Technology	6		269	274
160	Single crystalline germanium-lead formed by laser-induced epitaxy	Zhou Q., Ong E.B.L., Lim S.L., Vajandar S., Osipowicz T., Gong X., Tok E.S., Ye Y.-C.	2016	ECS Journal of Solid State Science and Technology	5		P353	P360
159	Etching of germanium-tin using ammonia peroxide mixture	Dong Y., Ong B.L., Wang W., Zhang Z., Pan J., Gong X., Tok E.S., Liang G., Yeo Y.-C.	2015	Journal of Applied Physics	118	245303		
158	Micro-dressing of a carbon nanotube array with MoS <sub>2</sub> gauze	Lim S.X., Woo K.W., Ng J., Lu J., Kwang S.Y., Zhang Z., Tok E.S., Sow C.-H.	2015	Nanoscale	7		17538	17546
157	Energy band alignment of SnO <sub>2</sub> /SrTiO <sub>3</sub> epitaxial heterojunction studied by X-ray photoelectron spectroscopy	Ke C., Zhu W., Zhang Z., Tok E.S., Pan J.	2015	Surface and Interface Analysis	47		824	827

156	Preservation of epoxy groups on surfaces in the covalent attachment of butadiene monoxide on Si(111)-(7×7): the effect of a vinyl substituent	Mao W., He J.H., Gu J.Q., Chen W., Wu K., Tok E.S., Xu G.Q.	2015	Chemical Communications	51		14195	14198
155	Post-growth annealing of germanium-tin alloys using pulsed excimer laser	Wang L., Wang W., Zhou Q., Pan J., Zhang Z., Tok E.S., Yeo Y.C.	2015	Journal of Applied Physics	118	25701		
154	Suppression of dark current in germanium-tin on silicon p-i-n photodiode by a silicon surface passivation technique	Dong Y., Wang W., Lei D., Gong X., Zhou Q., Lee S.Y., Loke W.K., Yoon S.-F., Tok E.S., Liang G., Yeo Y.-C.	2015	Optics Express	23		18611	18619
153	Self-assembly of tin wires via phase transformation of heteroepitaxial germanium-tin on germanium substrate	Wang W., Li L., Tok E.S., Yeo Y.-C.	2015	Journal of Applied Physics	117	225304		
152	Critical thickness for strain relaxation of Ge <sub>1-x</sub> Sn <sub>x</sub> (x ≤ 0.17) grown by molecular beam epitaxy on Ge(001)	Wang W., Zhou Q., Dong Y., Tok E.S., Yeo Y.-C.	2015	Applied Physics Letters	106	232106		
151	Influence of hydrogen surface passivation on Sn segregation, aggregation, and distribution in GeSn/Ge(001) materials	Johll H., Samuel M., Koo R.Y., Kang H.C., Yeo Y.-C., Tok E.S.	2015	Journal of Applied Physics	117	205302		
150	Detrimental effects of oxygen vacancies in electrochromic molybdenum oxide	Dasgupta B., Ren Y., Wong L.M., Kong L., Tok E.S., Chim W.K., Chiam S.Y.	2015	Journal of Physical Chemistry C	119		10592	10601
149	Atomic healing of defects in transition metal dichalcogenides	Lu J., Carvalho A., Chan X.K., Liu H., Liu B., Tok E.S., Loh K.P., Castro Neto A.H., Sow C.H.	2015	Nano Letters	15		3524	3532
148	Optimization of gold nanoparticle photoluminescence by alkanethiolation	Lai S.-F., Tan H.-R., Tok E.S., Chen Y.-H., Ong E.B.L., Li M.-T., Chen Y.-Y., Chien F.-C., Chen P., Margaritondo G., Hwu Y.	2015	Chemical Communications	51		7954	7957
147	Microlandscaping of au nanoparticles on few-layer Mos <sub>2</sub> films for chemical sensing	Lu J., Lu J.H., Liu H., Liu B., Gong L., Tok E.S., Loh K.P., Sow C.H.	2015	Small	11		1792	1800
146	Spontaneous decoration of Au nanoparticles on micro-patterned reduced graphene oxide shaped by focused laser beam	Wan Y.C., Teoh H.F., Tok E.S., Sow C.H.	2015	Journal of Applied Physics	117	54304		
145	Effect of orbital and ionic dynamics coupling in barrier crossing rates for Car-Parrinello molecular dynamics	Mohanam L.N., Ong S.W., Tok E.S., Kang H.C.	2015	Chemical Physics Letters	621		146	154
144	Nucleation and growth of Ge nanoclusters on the Si(111)-(7 x 7) surface studied by scanning tunneling microscopy	Zhang Y., Chen Z., Xu G.Q., Tok E.S.	2015	Surface and Interface Analysis	47		222	226
143	X-ray-induced Cu deposition and patterning on insulators at room temperature	Hsu P.-C., Chen Y.-S., Hwu Y., Je J.H., Margaritondo G., Tok E.S.	2015	Journal of Synchrotron Radiation	22		1524	1527
142	Gold nanoparticles: BSA (Bovine Serum Albumin) coating and X-ray irradiation produce variable-spectrum photoluminescence	Lee K.-H., Lai S.-F., Lin Y.-C., Chou W.-C., Ong E.B.L., Tan H.-R., Tok E.S., Yang C.S., Margaritondo G., Hwu Y.	2015	Materials Chemistry and Physics	149		582	586
141	Influence of interconfigurational electronic states on Fe, Co, Ni-silicene materials selection for spintronics	Johll H., Lee M.D.K., Ng S.P.N., Kang H.C., Tok E.S.	2014	Scientific Reports	4	7594		

140	Tin surface segregation, desorption, and island formation during post-growth annealing of strained epitaxial Ge <sub>1-x</sub> Sn <sub>x</sub> layer on Ge(0 0 1) substrate	Wang W., Li L., Zhou Q., Pan J., Zhang Z., Tok E.S., Yeo Y.-C.	2014	Applied Surface Science	321		240	244
139	Towards simultaneous achievement of carrier activation and crystallinity in Ge and GeSn with heated phosphorus ion implantation: An optical study	D'Costa V.R., Wang L., Wang W., Lim S.L., Chan T.K., Chua L.H., Henry T., Zou W., Hatem C., Osipowicz T., Tok E.S., Yeo Y.-C.	2014	Applied Physics Letters	105	122108		
138	Reaction mechanism and regioselectivity of methyl oxirane on Si(111)-(7 × 7)	Mao W., He J.H., Gu J.Q., Xu G.Q., Tok E.S.	2014	Journal of Physical Chemistry C	118		21509	21516
137	Band alignment study of lattice-matched In <sub>0.49</sub> Ga <sub>0.51</sub> P and Ge using x-ray photoelectron spectroscopy	Owen M.H.S., Zhou Q., Gong X., Zhang Z., Pan J.S., Loke W.K., Wicaksono S., Yoon S.F., Tok E.S., Yeo Y.-C.	2014	Applied Physics Letters	105	101604		
136	Compositional dependence of optical critical point parameters in pseudomorphic GeSn alloys	D'Costa V.R., Wang W., Zhou Q., Chan T.K., Osipowicz T., Tok E.S., Yeo Y.-C.	2014	Journal of Applied Physics	116	53520		
135	Band alignment of HfO <sub>2</sub> /In <sub>0.18</sub> Al <sub>0.82</sub> N determined by angle-resolved x-ray photoelectron spectroscopy	Owen M.H.S., Bhuiyan M.A., Zhang Z., Pan J.S., Tok E.S., Yeo Y.-C.	2014	Applied Physics Letters	105	31602		
134	Laser-induced greenish-blue photoluminescence of mesoporous silicon nanowires	Choi Y.-R., Zheng M., Bai F., Liu J., Tok E.-S., Huang Z., Sow C. H.	2014	Scientific Reports	4	4940		
133	Enhanced electrochemical etching of ion irradiated silicon by localized amorphization	Dang Z.Y., Breese M.B.H., Lin Y., Tok E.S., Vittone E.	2014	Applied Physics Letters	104	192108		
132	Orbital resolution of molecules covalently attached to a clean semiconductor surface	He J.H., Mao W., Xu G.Q., Tok E.S.	2014	Nature Communications	5	3721		
131	Microlandscaping on a graphene oxide film via localized decoration of Ag nanoparticles	Teoh H.F., Dzung P., Lim W.Q., Chua J.H., Lee K.K., Hu Z., Tan H., Tok E.S., Sow C.H.	2014	Nanoscale	6		3143	3149
130	Direct laser micropatterning of GeSe <sub>2</sub> nanostructures film with controlled optoelectrical properties	Mukherjee B., Murali G., Lim S.X., Zheng M., Tok E.S., Sow C.H.	2014	RSC Advances	4		10013	10021
129	Above-bandgap optical properties of biaxially strained GeSn alloys grown by molecular beam epitaxy	Richard D'Costa V., Wang W., Zhou Q., Soon Tok E., Yeo Y.-C.	2014	Applied Physics Letters	104	22111		
128	Silicon surface passivation technology for germanium-tin p-channel MOSFETs: Suppression of germanium and tin segregation for mobility enhancement	Guo P., Cheng R., Wang W., Zhang Z., Pan J., Tok E.S., Yeo Y.-C.	2014	ECS Journal of Solid State Science and Technology	3		Q162	Q168
127	Laser modified ZnO/CdSe core-shell nanowire arrays for micro-steganography and improved photoconduction	Lu J., Liu H., Zheng M., Zhang H., Lim S.X., Tok E.S., Sow C.H.	2014	Scientific Reports	4	6350		
126	Germanium-tin P-channel field-effect transistor with low-temperature Si <sub>2</sub> H <sub>6</sub> passivation	Gong X., Yang Y., Guo P., Wang W., Cheng R., Wang L., Tok E.S., Yeo Y.-C.	2014	ECS Transactions	64		851	868
125	Strain-induced morphological instability and self assembly of tin wires during controlled annealing of Ge <sub>0.83</sub> Sn <sub>0.17</sub> epitaxial film on Ge(001) substrate	Li L., Wang W., Tok E.S., Yeo Y.-C.	2014	2014 7th International Silicon-Germanium Technology and Device Meeting		6874671	45	46

124	Growth of tensile-strained Ge layer and highly strain-relaxed Ge 1-xSnx buffer layer on silicon by molecular beam epitaxy	Wang W., Tok E.S., Yeo Y.-C.	2014	2014 7th International Silicon-Germanium Technology and Device Meeting		6874669	81	82
123	Single crystalline germanium-lead alloy on germanium substrate formed by pulsed laser epitaxy	Zhou Q., Chan T.K., Lim S.L., Zhan C., Osipowicz T., Gong X., Tok E.S., Yeo Y.-C.	2014	ECS Solid State Letters	3		P91	P93
122	High mobility germanium-tin (Ge <sub>0.930</sub> Sn <sub>0.070</sub> ) P-MOSFETs with surface passivation by silicon atomic layer epitaxy	Lei D., Zhan C., Wang W., Gong X., Zhou Q., Tok E.-S., Yeo Y.-C.	2014	2014 7th International Silicon-Germanium Technology and Device Meeting		6874663	147	148
121	Thermal stability of highly compressive strained germanium-tin (GeSn) grown by molecular beam epitaxy	Wang W., Zhou Q., Pan J., Zhang Z., Tok E.S., Yeo Y.-C.	2014	2014 7th International Silicon-Germanium Technology and Device Meeting		6874668	157	158
120	Germanium-lead alloy with 0.3% substitutional lead formed by pulsed laser induced epitaxy	Zhou Q., Zhan C., Gong X., Chan T.K., Osipowicz T., Lim S.L., Tok E.S., Yeo Y.-C.	2014	2014 7th International Silicon-Germanium Technology and Device Meeting		6874665	79	80
119	Single crystalline germanium-lead alloy on germanium substrate formed by pulsed laser epitaxy	Zhou Q., Chan T.K., Lim S.L., Zhan C., Osipowicz T., Gong X., Tok E.S., Yeo Y.-C.	2014	ECS Electrochemistry Letters	3		P91	P93
118	NIR schottky photodetectors based on individual single-crystalline GeSe nanosheet	Mukherjee B., Cai Y., Tan H.R., Feng Y.P., Tok E.S., Sow C.H.	2013	ACS Applied Materials and Interfaces	5		9594	9604
117	Photocurrent characteristics of individual GeSe <sub>2</sub> nanobelt with Schottky effects	Mukherjee B., Tok E.S., Sow C.H.	2013	Journal of Applied Physics	114	134302		
116	Self-assembled molecular wires and highly ordered monolayer: Thiazole on Ge(100)	He J.H., Mao W., Gu J.Q., Xu G.Q., Tok E.S.	2013	Journal of Physical Chemistry C	117		19115	19118
115	Shape transition of endotaxial islands growth from kinetically constrained to equilibrium regimes	Li Z.-P., Tok E., Foo Y.	2013	Materials Research Bulletin	48		2998	3008
114	Germanium-Tin (GeSn) N-channel MOSFETs with low temperature silicon surface passivation	Guo P., Zhan C., Yang Y., Gong X., Liu B., Cheng R., Wang W., Pan J., Zhang Z., Tok E.S., Han G., Yeo Y.-C.	2013	2013 International Symposium on VLSI Technology, Systems and Applications - VLSI		6545615		
113	Ge <sub>0.97</sub> Sn <sub>0.03</sub> p-channel metal-oxide-semiconductor field-effect transistors: Impact of Si surface passivation layer thickness and post metal annealing	Guo P., Han G., Gong X., Liu B., Yang Y., Wang W., Zhou Q., Pan J., Zhang Z., Soon Tok E., Yeo Y.-C.	2013	Journal of Applied Physics	114	44510		
112	Field emission from decorated carbon nanotube-QDs microstructures with a view to the dominant electron paths	Lim S.X., Chang S.L., Cheong F.C., Tok E.S., Zhang Z., Lim C.T., Sow C.-H.	2013	Journal of Physical Chemistry C	117		14408	14417
111	K-Enriched WO <sub>3</sub> nanobundles: High electrical conductivity and photocurrent with controlled polarity	Hu Z., Ji Z., Lim W.W., Mukherjee B., Zhou C., Tok E.S., Sow C.-H.	2013	ACS Applied Materials and Interfaces	5		4731	4738
110	Enhanced extraction rates through gap states of molybdenum oxide anode buffer	Dasgupta B., Goh W.P., Ooi Z.E., Wong L.M., Jiang C.Y., Ren Y., Tok E.S., Pan J., Zhang J., Chiam S.Y.	2013	Journal of Physical Chemistry C	117		9206	9211
109	Very small photoluminescent gold nanoparticles for multimodality biomedical imaging	Lai S.-F., Chien C.-C., Chen W.-C., Chen H.-H., Chen Y.-Y., Wang C.-L., Hwu Y., Yang C.S., Chen C.Y., Liang K.S., Petibois C., Tan H.-R., Tok E.-S., Margaritondo G.	2013	Biotechnology Advances	31		362	368

108	Interaction of magnetic transition metal dimers with spin-polarized hydrogenated graphene	Ong S.W., Wu J., Thong A.Z.H., Tok E.S., Kang H.C.	2013	Journal of Chemical Physics	138	124709		
107	Germanium-tin (GeSn) p-channel MOSFETs fabricated on (100) and (111) surface orientations with Sub-400 °C Si <sub>2</sub> H <sub>6</sub> passivation	Gong X., Han G., Bai F., Su S., Guo P., Yang Y., Cheng R., Zhang D., Zhang G., Xue C., Cheng B., Pan J., Zhang Z., Tok E.S., Antoniadis D., Yeo Y.-C.	2013	IEEE Electron Device Letters	34	6415984	339	341
106	Desorption of ambient gas molecules and phase transformation of $\alpha$ -Fe <sub>2</sub> O <sub>3</sub> nanostructures during ultrahigh vacuum annealing	Zhang Z., Lu J., Yun T., Zheng M., Pan J., Sow C.H., Tok E.S.	2013	Journal of Physical Chemistry C	117		1509	1517
105	Stepped-surfaced GeSe <sub>2</sub> nanobelts with high-gain photoconductivity	Mukherjee B., Hu Z., Zheng M., Cai Y., Feng Y.P., Tok E.S., Sow C.H.	2012	Journal of Materials Chemistry	22		24882	24888
104	Localized photo-induced voltage with controlled polarity in single K enriched MoO <sub>3</sub> nanobundle	Hu Z., Tok E.S., Sow C.H.	2012	Nanotechnology	23	475204		
103	Growth dynamics of low-dimensional CoSi <sub>2</sub> nanostructures revisited: Influence of interface structure and growth temperature	Ong B.L., Ong W., Foo Y.L., Pan J., Tok E.S.	2012	Surface Science	606		1649	1669
102	Anomalous scaling behaviour of cobalt cluster size distributions on graphite, epitaxial graphene and carbon-rich (6 $\sqrt{3}$ $\times$ 6 $\sqrt{3}$ )R30°	Poon S.W., Wee A.T.S., Tok E.S.	2012	Surface Science	606		1586	1593
101	Endoepitaxial growth of hexagonal-Fe <sub>13</sub> Ge <sub>8</sub> islands on Cubic-Ge(001)	Li Z.-P., Tok E.S., Foo Y.L.	2012	Journal of Physics and Chemistry of Solids	73		1213	1217
100	Direct laser-enabled graphene oxide-Reduced graphene oxide layered structures with micropatterning	Fatt Teoh H., Tao Y., Soon Tok E., Wei Ho G., Haur Sow C.	2012	Journal of Applied Physics	112	64309		
99	Sub-bandgap energy photoresponse of individual V <sub>2</sub> O <sub>5</sub> nanowires	Tamang R., Varghese B., Tok E.S., Mhaisalkar S., Sow C.H.	2012	Nanoscience and Nanotechnology Letters	4		716	719
98	Real time dynamics of Si magic clusters mediating phase transformation: Si(111)-(1 $\times$ 1) to (7 $\times$ 7) reconstruction revisited	Ong W.J., Tok E.S.	2012	Surface Science	606		1037	1044
97	Temperature-dependent phase separation during annealing of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films in vacuum	Zhang Z., Pan J., Fang L.W.-W., Yeo Y.-C., Foo Y.L., Zhao R., Shi L., Tok E.S.	2012	Applied Surface Science	258		6075	6079
96	Electrical and photoresponse properties of Co <sub>3</sub> O <sub>4</sub> nanowires	Varghese B., Mukherjee B., Karthik K.R.G., Jinesh K.B., Mhaisalkar S.G., Soon Tok E., Haur Sow C.	2012	Journal of Applied Physics	111	104306		
95	Unique geometric and electronic structure of CO adsorbed on Ge(100): A DFT study	He J.H., Zhang Y.P., Mao W., Xu G.Q., Tok E.S.	2012	Surface Science	606		784	790
94	Synthesis, characterization and electrical properties of hybrid Zn <sub>2</sub> GeO <sub>4</sub> -ZnO beaded nanowire arrays	Mukherjee B., Varghese B., Zheng M., Karthik K.R.G., Mathews N., Mhaisalkar S.G., Tok E.S., Sow C.H.	2012	Journal of Crystal Growth	346		32	39
93	$\alpha$ -Fe <sub>2</sub> O <sub>3</sub> nanotubes-reduced graphene oxide composites as synergistic electrochemical capacitor materials	Lee K.K., Deng S., Fan H.M., Mhaisalkar S., Tan H.R., Tok E.S., Loh K.P., Chin W.S., Sow C.H.	2012	Nanoscale	4		2958	2961

92	Architecturing covalently bonded organic bilayers on the Si(111)-(7 × 7) surface via in situ photoinduced reaction	Zhang Y.P., He J.H., Xu G.Q., Tok E.S.	2012	Journal of Physical Chemistry C	116		8943	8949
91	Localized insulator-conductor transformation of graphene oxide thin films via focused laser beam irradiation	Tao Y., Varghese B., Jaiswal M., Wang S., Zhang Z., Oezylmaz B., Loh K.P., Tok E.S., Sow C.H.	2012	Applied Physics A: Materials Science and Processing	106		523	531
90	In situ observation of self-assembled Fe <sub>13</sub> Ge <sub>8</sub> nanowires growth on anisotropic Ge (1 1 0) surface	Li Z.-P., Tok E., Foo Y.	2012	Materials Research Bulletin	47		438	444
89	Evidence for the interfacial reaction between Ni adatoms and H-Si(001) surface	Zhang Z., Pan J.S., Chai J.W., Zhang J., Tok E.S.	2011	Surface Science	605		1852	1860
88	Nonvolatile rewritable memory effects in graphene oxide functionalized by conjugated polymer containing fluorene and carbazole units	Zhang B., Liu Y.-L., Chen Y., Neoh K.-G., Li Y.-X., Zhu C.-X., Tok E.-S., Kang E.-T.	2011	Chemistry - A European Journal	17		10304	10311
87	Selective attachment of 4-bromostyrene on the Si(111)-(7 × 7) surface	Zhang Y.P., He J.H., Xu G.Q., Tok E.S.	2011	Journal of Physical Chemistry C	115		15496	15501
86	One-pot tuning of Au nucleation and growth: From nanoclusters to nanoparticles	Lai S.-F., Chen W.-C., Wang C.-L., Chen H.-H., Chen S.-T., Chien C.-C., Chen Y.-Y., Hung W.-T., Cai X., Li E., Kempson I.M., Hwu Y., Yang C.S., Tok E.-S., Tan H.R., Lin M., Margaritondo G.	2011	Langmuir	27		8424	8429
85	Graphene-adsorbed Fe, Co, and Ni trimers and tetramers: Structure, stability, and magnetic moment	Johll H., Wu J., Ong S.W., Kang H.C., Tok E.S.	2011	Physical Review B - Condensed Matter and Materials Physics	83	205408		
84	Electrical current mediated interconversion between graphene oxide to reduced graphene oxide	Teoh H.F., Tao Y., Tok E.S., Ho G.W., Sow C.H.	2011	Applied Physics Letters	98	173105		
83	Probing the photoresponse of individual Nb <sub>2</sub> O <sub>5</sub> nanowires with global and localized laser beam irradiation	Tamang R., Varghese B., Mhaisalkar S.G., Tok E.S., Sow C.H.	2011	Nanotechnology	22	115202		
82	Tuning molecular binding configurations of pyridine on Si(111)-(7 × 7) via surface modification	Zhang Y.P., Wang S., Xu G.Q., Tok E.S.	2011	Journal of Physical Chemistry C	115		2140	2145
81	Structure and properties of pure and mixed transition metal dimers on graphene	Johll H., Tok E.S., Kang H.C.	2011	International Journal of Nanotechnology	8		825	840
80	Hydrogen adsorption on mixed platinum and nickel nanoclusters: The influence of cluster composition and graphene support	Wu J., Ong S.W., Kang H.C., Tok E.S.	2010	Journal of Physical Chemistry C	114		21252	21261
79	Vibrational frequencies in Car-Parrinello molecular dynamics	Ong S.W., Tok E.S., Kang H.C.	2010	Physical Chemistry Chemical Physics	12		14960	14966
78	Growth dynamics and kinetics of monolayer and multilayer graphene on a 6H-SiC(0001) substrate	Poon S.W., Chen W., Wee A.T.S., Tok E.S.	2010	Physical Chemistry Chemical Physics	12		13522	13533
77	In situ ultrahigh vacuum transmission electron microscopy study of quasi-one-dimensional island decay on isotropic Ge(001) surface	Li Z.-P., Tok E.S., Foo Y.L.	2010	Journal of Applied Physics	108	84310		



76	Photothermoelectric effects in localized photocurrent of individual vo 2 nanowires	Varghese B., Tamang R., Tok E.S., Mhaisalkar S.G., Sow C.H.	2010	Journal of Physical Chemistry C	114		15149	15156
75	Revisiting the vibrational spectra of silicon hydrides on Si (100) - (2×1) surface: What is on the surface when disilane dissociates?	Ong S.W., Tok E.S., Kang H.C.	2010	Journal of Chemical Physics	133	74708		
74	Kinetics of Ge diffusion, desorption and pit formation dynamics during annealing of Si <sub>0.8</sub> Ge <sub>0.2</sub> /Si(001) virtual substrates	Zhang Z., Pan J.S., Zhang J., Tok E.S.	2010	Physical Chemistry Chemical Physics	12		7171	7183
73	Disilane chemisorption on Six Ge <sub>1-x</sub> (100) - (2×1): Molecular mechanisms and implications for film growth rates	Ng R.Q.-M., Tok E.S., Kang H.C.	2009	Journal of Chemical Physics	131	44707		
72	Volatile electrical switching and static random access memory effect in a functional polyimide containing oxadiazole moieties	Liu Y.-L., Wang K.-L., Huang G.-S., Zhu C.-X., Tok E.-S., Neoh K.-G., Kang E.-T.	2009	Chemistry of Materials	21		3391	3399
71	Self-assembly, dynamics, and structure of Si magic clusters	Ong W., Tok E.S., Johll H., Kang H.C.	2009	Physical Review B - Condensed Matter and Materials Physics	79	235439		
70	Density functional theory study of Fe, Co, and Ni adatoms and dimers adsorbed on graphene	Johll H., Kang H.C., Tok E.S.	2009	Physical Review B - Condensed Matter and Materials Physics	79	245416		
69	Molecular mechanisms for disilane chemisorption on Si (100) - (2×1)	Ng R.Q.-M., Tok E.S., Kang H.C.	2009	Journal of Chemical Physics	130	114702		
68	Energetics of adsorbed hydrogen and surface germanium on stepped Six Ge <sub>1-x</sub> (100)-(2×1) surfaces	Li Q., Tok E.S., Kang H.C.	2008	Physical Review B - Condensed Matter and Materials Physics	77	205306		
67	Probing epitaxial growth of graphene on silicon carbide by metal decoration	Poon S.W., Chen W., Tok E.S., Wee A.T.S.	2008	Applied Physics Letters	92	104102		
66	The dissociative adsorption of silane and disilane on Si(100)-(2×1)	Shi J., Tok E.S., Kang H.C.	2007	Journal of Chemical Physics	127	164713		
65	Direct observation of carbon nanostructures growth using in-situ ultrahigh vacuum transmission electron microscopy	Foo Y.L., Lin M., Tan J.P.Y., Boothroyd C.B., Tok E.S.	2007	2007 NSTI Nanotechnology Conference and Trade Show - NSTI Nanotech 2007, Technical Proceedings	1		21	24
64	Dynamical observation of bamboo-like carbon nanotube growth	Lin M., Tan J.P.Y., Boothroyd C., Loh K.P., Tok E.S., Foo Y.-L.	2007	Nano Letters	7		2234	2238
63	Sputter roughening of inhomogeneous surfaces: Impurity pinning and nanostructure shape selection	Ong S.W., Tok E.S., Kang H.C.	2007	Physical Review E - Statistical, Nonlinear, and Soft Matter Physics	75	61607		
62	Kinetically constraint zero- and one-dimensional heteroepitaxial island growth	Li Z., Singh M.K., Tok E.S., Tan J.P.Y., Lin M., Foo Y.-L.	2007	Applied Physics Letters	90	101914		

61	Reassessment of the molecular mechanisms for H <sub>2</sub> thermal desorption pathways from Si(1-x)Ge <sub>x</sub> (001)-(2×1) surfaces	Li Q., Tok E.S., Zhang J., Chuan Kang H.	2007	Journal of Chemical Physics	126	44706		
60	Configuration dependent critical nuclei in the self assembly of magic clusters	Ong W.J., Tok E.S.	2007	Physical Chemistry Chemical Physics	9		991	995
59	Decomposition of Si H <sub>3</sub> to Si H <sub>2</sub> on Si(100)- (2x1)	Lim F.C.H., Tok E.S., Kang H.C.	2006	Physical Review B - Condensed Matter and Materials Physics	74	205333		
58	Adsorption and diffusion of Co on the Si(001) surface	Peng G.W., Huan A.C.H., Tok E.S., Feng Y.P.	2006	Physical Review B - Condensed Matter and Materials Physics	74	195335		
57	Erratum: Nucleation and growth of cobalt nanostructures on highly oriented pyrolytic graphite (Physical Chemistry Chemical Physics (2006) 8 (3326) DOI: 10.1039/b604627b)	Poon S.W., Pan J.S., Tok E.S.	2006	Physical Chemistry Chemical Physics	8		5132	
56	C <sub>60</sub> on SiC nanomesh	Chen W., Zhang H.L., Xu H., Tok E.S., Loh K.P., Wee A.T.S.	2006	Journal of Physical Chemistry B	110		21873	21881
55	Nucleation and growth of cobalt nanostructures on highly oriented pyrolytic graphite	Poon S.W., Pan J.S., Tok E.S.	2006	Physical Chemistry Chemical Physics	8		3326	3334
54	Sharp n-type doping profiles in Si/SiGe heterostructures produced by atomic hydrogen etching	Zhang J., Turner S.G., Chiam S.Y., Liu R., Tok E.S., Wee A.T.S., Huan A.C.H., Kelly I., Mulcahy C.P.A.	2006	Surface Science	600		2288	2292
53	Co growth on Si(0 0 1) and Si(1 1 1) surfaces: Interfacial interaction and growth dynamics	Pan J.S., Liu R.S., Zhang Z., Poon S.W., Ong W.J., Tok E.S.	2006	Surface Science	600		1308	1318
52	Direct observation of single-walled carbon nanotube growth at the atomistic scale	Lin M., Tan J.P.Y., Boothroyd C., Loh K.P., Tok E.S., Foo Y.-L.	2006	Nano Letters	6		449	452
51	Role of Si clusters in the phase transformation and formation of (6x6) -ring structures on 6H-SiC(0001) as a function of temperature: An STM and XPS study	Ong W.J., Tok E.S.	2006	Physical Review B - Condensed Matter and Materials Physics	73	45330		
50	Probing Co/Si interface behaviour by X-ray photoelectron spectroscopy (XPS) and atomic force microscopy (AFM)	PAN J.S.P, LIU R.S.L, TOK E.S.T	2006	Nuclear Science and Techniques/Hew uli	17		202	211
49	Observation of local lattice tilts in strain-relaxed Si 1-xGe <sub>x</sub> using high resolution channeling contrast microscopy	Seng H.L., Osipowicz T., Zhang J., Tok E.S.	2005	Applied Physics A: Materials Science and Processing	81		1163	1166
48	Tungsten nanocrystals embedded in high- k materials for memory application	Samanta S.K., Yoo W.J., Samudra G., Tok E.S., Bera L.K., Balasubramanian N.	2005	Applied Physics Letters	87	113110		
47	Evidence for hydrogen desorption through both interdimer and intradimer paths from Si(100)-(2×1)	Shi J., Kang H.C., Tok E.S., Zhang J.	2005	Journal of Chemical Physics	123	34701		

46	Determination of local lattice tilt in Si <sub>1-x</sub> Ge <sub>x</sub> virtual substrate using high resolution channeling contrast microscopy	Seng H.L., Osipowicz T., Zhang J., Tok E.S., Watt F.	2005	Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with Materials and Atoms	231		446	451
45	Dynamical scaling of sputter-roughened surfaces in 2+1 dimensions	Tok E.S., Ong S.W., Kang H.C.	2004	Physical Review E - Statistical, Nonlinear, and Soft Matter Physics	70	11604	11604	-011604-
44	6H-SiC(0 0 1) phase transition: Evolution of the (6 × 6) magic clusters	Tok E.S., Ong W.J., Wee A.T.S.	2004	Surface Science	558		145	158
43	Hydrogen desorption kinetics from the Si (1 - x)Ge <sub>x</sub> (100)-(2×1) surface	Tok E.S., Ong S.W., Kang H.C.	2004	Journal of Chemical Physics	120		5424	5431
42	Dynamical scaling of sputter-roughened surfaces in [Formula presented] dimensions	Tok E.S., Ong S.W., Kang H.C.	2004	Physical Review E - Statistical Physics, Plasmas, Fluids, and Related Interdisciplinary Topics	70		6	
41	Roughening behavior in Si/SiGe heterostructures under O <sub>2</sub> + bombardment	Lau G.S., Tok E.S., Liu R., Wee A.T.S., Zhang J.	2004	Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with	215		76	82
40	Nanostructure formation by O <sub>2</sub> <sup>+</sup> ion sputtering of Si/SiGe heterostructures	Lau G.S., Tok E.S., Liu R., Wee A.T.S., Tjiu W.C., Zhang J.	2003	Nanotechnology	14		1187	1191
39	High-resolution channeling contrast microscopy of compositionally graded Si <sub>1-x</sub> Ge <sub>x</sub> layers	Seng H.L., Osipowicz T., Sum T.C., Breese M.B.H., Watt F., Tok E.S., Zhang J.	2003	Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with	210		483	488
38	Probing the behaviour of ultra thin Co layers on clean and hydrogen terminated Si(0 0 1) and Si(1 1 1) surfaces	Pan J.S., Tok E.S., Huan C.H.A., Liu R.S., Chai J.W., Ong W.J., Toh K.C.	2003	Surface Science	532-535		639	644
37	The effects of carbon incorporation during GSMBE of Si <sub>1-y</sub> Cy and Si <sub>1-x-y</sub> Ge <sub>x</sub> Cy: Growth dynamics and segregation	Price R.W., Tok E.S., Woods N.J., Zhang J.	2003	Surface Science	532-535		905	910
36	Phosphorus incorporation during InP(0 0 1) homoepitaxial growth by solid source molecular beam epitaxy	Barnes G.W., Tok E.S., Neave J.H., Jones T.S.	2003	Surface Science	531		L383	L387
35	Dynamics and surface segregation during GSMBE of Si <sub>1-y</sub> Cy and Si <sub>1-x-y</sub> Ge <sub>x</sub> Cy on the Si(0 0 1) surface	Price R.W., Tok E.S., Liu R., Wee A.T.S., Woods N.J., Zhang J.	2003	Journal of Crystal Growth	251		676	680
34	Precursor states of atomic hydrogen on the Si(100)-(2×1) surface	Tok E.S., Engstrom J.R., Kang H.C.	2003	Journal of Chemical Physics	118		3294	3299
33	Growth dynamics of Si <sub>1-y</sub> Cy and Si <sub>1-x-y</sub> Ge <sub>x</sub> Cy on Si(001) surface from disilane, germane, and methylsilane	Price R.W., Tok E.S., Woods N.J., Zhang J.	2002	Applied Physics Letters	81		3780	3782
32	On STM imaging of GaAs(0 0 1)-(n × 6) surface reconstructions: Does the (6 × 6) structure exist?	Xu H., Li Y.G., Wee A.T.S., Huan C.H.A., Tok E.S.	2002	Surface Science	513		249	255

31	Self-assembly of Si nanoclusters on 6H-SiC(0001)-(3×3) reconstructed surface	Ong W.J., Tok E.S., Xu H., Wee A.T.S.	2002	Applied Physics Letters	80		3406	3408
30	High resolution channeling contrast microscopy and channeling analysis of SiGe quantum well structures	Osipowicz T., Seng H.L., Wielunski L.S., Tok E.S., Breton G., Zhang J.	2002	Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with	190		345	350
29	Optimal geometry for GeSi/Si super-lattice structure RBS investigation	Wielunski L.S., Osipowicz T., Teo E.J., Watt F., Tok E.S., Zhang J.	2002	Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with	190		414	418
28	Probing the SiGe virtual substrate by high-resolution channeling contrast microscopy	Seng H.L., Osipowicz T., Sum T.C., Tok E.S., Breton G., Woods N.J., Zhang J.	2002	Applied Physics Letters	80		2940	2942
27	Growth mechanisms in thin film epitaxy of Si/SiGe from hydrides	Zhang J., Woods N.J., Breton G., Price R.W., Hartell A.D., Lau G.S., Liu R., Wee A.T.S., Tok E.S.	2002	Materials Science and Engineering B: Solid-State Materials for Advanced Technology	89		399	405
26	Dynamics and surface segregation during GSMBE of Si <sub>1-y</sub> Cy and Si <sub>1-x-y</sub> GexCy on the Si[001] surface	Price R.W., Tok E.S., Liu R., Wee A.T.S., Woods N.J., Zhang J.	2002	MBE 2002 - 2002 12th International Conference on Molecular Beam Epitaxy		1037756	53	54
25	Comment on "A new mechanism for reentrant behaviour in semiconductor epitaxy: A reflection high-energy electron diffraction study of the growth of GaAs(1 1 1)A thin films" [Surf. Sci. 459 (2000) 277-286]	Tok E.S., Neave J.H., Zhang J.	2002	Surface Science	515		263	265
24	The investigation of surface topography development in Si(001) and Si(111) during SIMS depth profiling	Lau G.S., Tok E.S., Wee A.T.S., Liu R., Lim S.L.	2001	Surface Review and Letters	8		453	457
23	Missing "sheets" in the reciprocal space representation of the disordered surface with one-dimensional domain boundaries	Tok E.S., Zhang J., Kamiya I., Xie M.H., Neave J.H., Joyce B.A.	2001	Surface Review and Letters	8		509	511
22	Reaction path for hydrogen adsorption and desorption on Si(100)-(2×1)	Tok E.S., Kang H.C.	2001	Journal of Chemical Physics	115		6550	6556
21	The development of RAS and RHEED as in situ probes to monitor dopant segregation in GS-MBE on Si (0 0 1)	Hartell A.D., Tok E.S., Zhang J.	2001	Journal of Crystal Growth		227-228	729	734
20	Kinetics of Si growth from hydride precursors on As-passivated Si(001) surface	Tok E.S., Hartell A.D., Zhang J.	2001	Applied Physics Letters	78		919	921
19	Thin film epitaxy on Si for microelectronics	Zhang J., Tok E.S., Breton G., Woods N.J.	2000	Proceedings of SPIE - The International Society for Optical Engineering		4227	1	8
18	Adsorption and coadsorption of hydrogen and fluorine on the Si(100)-(2×1) surface	Yang C., Kang H.C., Tok E.S.	2000	Surface Science	465		9	18
17	Oscillatory optical second-harmonic generation from Si(001) surface during thin-film epitaxy	Tok E.S., Price R.W., Taylor A.G., Zhang J.	2000	Applied Physics Letters	76		933	935

16	RHEED and SIMS studies of germanium segregation during growth of SiGe/Si heterostructures; A two-site exchange model with growth rate dependence	Tok E.S., Woods N.J., Zhang J.	2000	Journal of Crystal Growth	209		321	326
15	Probing the silane, disilane and germane adsorption kinetics on the silicon (0 0 1) surface	Price R.W., Tok E.S., Zhang J.	2000	Journal of Crystal Growth	209		306	310
14	Optical second harmonic generation studies of epitaxial growth of Si and SiGe	Tok E.S., Woods N.J., Price R.W., Taylor A.G., Zhang J.	2000	Journal of Crystal Growth	209		297	301
13	Re-entrant behaviour in GaAs(1 1 1)A homoepitaxy	Steans P.H., Neave J.H., Zhang J., Tok E.S., Bell G.R., Joyce B.A., Jones T.S.	1999	Journal of Crystal Growth	201		198	201
12	Probing the disilane adsorption kinetics: an alternative approach	Price R.W., Tok E.S., Zhang J.	1999	Physical Review B - Condensed Matter and Materials Physics	59		R5292	R5295
11	Surface evolution in GaAs(1 1 0) homoepitaxy; from microscopic to macroscopic morphology	Holmes D.M., Tok E.S., Sudijono J.L., Jones T.S., Joyce B.A.	1998	Journal of Crystal Growth	192		33	46
10	Growth of Si-doped GaAs(110) thin films by molecular beam epitaxy; Si site occupation and the role of arsenic	Tok E.S., Neave J.H., Ashwin M.J., Joyce B.A., Jones T.S.	1998	Journal of Applied Physics	83		4160	4167
9	Stoichiometry and discommensuration on reconstructed surfaces: A quantitative x-ray diffuse-scattering study	Garreau Y., Aïd K., Sauvage-Simkin M., Pinchaux R., McConville C., Jones T., Sudijono J., Tok E.	1998	Physical Review B - Condensed Matter and Materials Physics	58		16177	16185
8	Is the arsenic incorporation kinetics important when growing GaAs(001), (110), and (111)A films?	Tok E.S., Jones T.S., Neave J.H., Zhang J., Joyce B.A.	1997	Applied Physics Letters	71		3278	3280
7	MBE growth of lattice-matched and mismatched films on non-(001) GaAs substrates	Fahy M.R., Zhang X.M., Tok E.S., Neave J.H., Vaccaro P., Fujita K., Takahashi M., Watanabe T., Sato K., Joyce B.A.	1997	Thin Solid Films	306		192	197
6	Electrical properties of lateral p-n junctions formed on patterned (110) GaAs substrates	Gardner N.R., Woods N.J., Domínguez P.S., Tok E.S., Norman C.E., Harris J.J.	1997	Semiconductor Science and Technology	12		737	741
5	An STM study of the nature of the transitional phase of the GaAs(111) B surface	Avery A.R., Tok E.S., Jones T.S.	1997	Surface Science	376		L397	L402
4	Arsenic incorporation kinetics in GaAs(001) homoepitaxy revisited	Tok E.S., Neave J.H., Zhang J., Joyce B.A., Jones T.S.	1997	Surface Science	374		397	405
3	Incorporation kinetics of As <sub>2</sub> and As <sub>4</sub> on GaAs(110)	Tok E.S., Neave J.H., Allegretti F.E., Zhang J., Jones T.S., Joyce B.A.	1997	Surface Science	371		277	288
2	Influence of arsenic incorporation on surface morphology and Si doping in GaAs(110) homoepitaxy	Tok E.S., Neave J.H., Fahy M.R., Allegretti F.E., Zhang J., Jones T.S., Joyce B.A.	1997	Microelectronics Journal	28		833	839
1	Growth of poly(methyl methacrylate) particles in three-component cationic microemulsions	Gan L.M., Lee K.C., Chew C.H., Tok E.S., Ng S.C.	1995	Journal of Polymer Science Part A: Polymer Chemistry	33		1161	1168